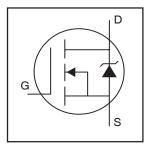
International Rectifier

IRF3205PbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



 $V_{DSS} = 55V$ $R_{DS(on)} = 8.0 \text{m}\Omega$ $I_D = 110 \text{A}^{\circ}$

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Absolute Maximum Ratings

	Parameter	Max.	Units	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	110 ⑤		
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	80	Α	
I _{DM}	Pulsed Drain Current ①	390]	
P _D @T _C = 25°C	Power Dissipation	200	W	
	Linear Derating Factor	1.3	W/°C	
V_{GS}	Gate-to-Source Voltage	± 20	V	
I _{AR}	Avalanche Current①	62	Α	
E _{AR}	Repetitive Avalanche Energy①	20	mJ	
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns	
T _J	Operating Junction and	-55 to + 175		
T _{STG}	Storage Temperature Range		°C	
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)		
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)		

Thermal Resistance

	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		0.75	
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.50		°C/W
$R_{\theta JA}$	Junction-to-Ambient		62	



Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		0.057		V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance			8.0	mΩ	V _{GS} = 10V, I _D = 62A ④
V _{GS(th)}	Gate Threshold Voltage	2.0		4.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
9 _{fs}	Forward Transconductance	44			S	V _{DS} = 25V, I _D = 62A⊕
I _{DSS}	Drain-to-Source Leakage Current			25	μA	$V_{DS} = 55V, V_{GS} = 0V$
				250		$V_{DS} = 44V, V_{GS} = 0V, T_{J} = 150^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			100	nA	$V_{GS} = 20V$
.033	Gate-to-Source Reverse Leakage			-100	117 ($V_{GS} = -20V$
Q_g	Total Gate Charge			146		$I_D = 62A$
Q _{gs}	Gate-to-Source Charge			35	nC	$V_{DS} = 44V$
Q _{gd}	Gate-to-Drain ("Miller") Charge			54		V_{GS} = 10V, See Fig. 6 and 13
t _{d(on)}	Turn-On Delay Time		14			$V_{DD} = 28V$
t _r	Rise Time		101		ns	$I_D = 62A$
t _{d(off)}	Turn-Off Delay Time		50		115	$R_G = 4.5\Omega$
t _f	Fall Time		65			V _{GS} = 10V, See Fig. 10 ⊕
L _D	Internal Drain Inductance		4.5			Between lead,
					nH	6mm (0.25in.) from package
L _S	Internal Source Inductance		7.5			and center of die contact
C _{iss}	Input Capacitance		3247			$V_{GS} = 0V$
Coss	Output Capacitance		781			$V_{DS} = 25V$
C _{rss}	Reverse Transfer Capacitance		211		pF	f = 1.0MHz, See Fig. 5
E _{AS}	Single Pulse Avalanche Energy ^②		1050©	264⑦	mJ	$I_{AS} = 62A, L = 138\mu H$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			110	110	MOSFET symbol
	(Body Diode)		. 110	Α Α	showing the	
I _{SM}	Pulsed Source Current			000		integral reverse
	(Body Diode)①		390		p-n junction diode.	
V_{SD}	Diode Forward Voltage			1.3	V	$T_J = 25^{\circ}C$, $I_S = 62A$, $V_{GS} = 0V$ ④
t _{rr}	Reverse Recovery Time		69	104	ns	$T_J = 25^{\circ}C, I_F = 62A$
Q _{rr}	Reverse Recovery Charge		143	215	nC	di/dt = 100A/µs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- $\begin{tabular}{ll} \hline @ Starting $T_J = 25^\circ C$, $L = 138\mu H$ \\ $R_G = 25\Omega, I_{AS} = 62A. (See Figure 12) \\ \hline \end{tabular}$
- $\label{eq:loss} \begin{array}{l} \text{ } \exists \ \ I_{SD} \leq 62A, \ di/dt \leq 207A/\mu s, \ V_{DD} \leq V_{(BR)DSS}, \\ T_{J} \leq 175^{\circ}C \end{array}$
- $\ \, \mbox{ } \mbox$
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ⑤ This is a typical value at device destruction and represents operation outside rated limits.
- $\ensuremath{\mathfrak{D}}$ This is a calculated value limited to T_J = 175°C.

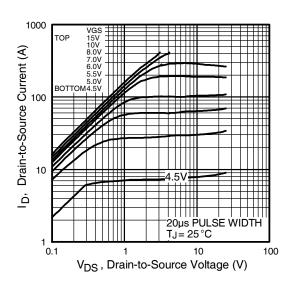
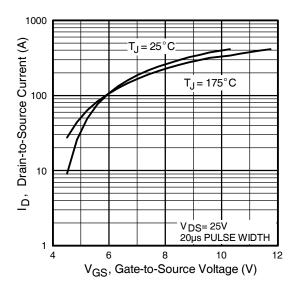


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics



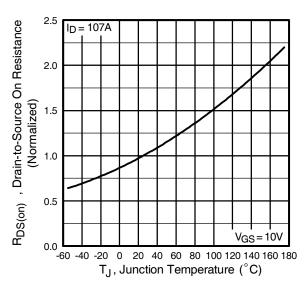
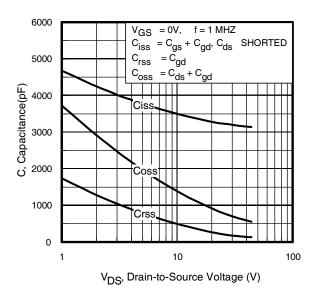


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

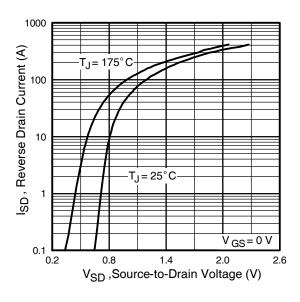
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16 ID = 62A V_{DS}= 44V V_{DS}= 27V V_{DS}= 11V V_{GS}, Gate-to-Source Voltage (V) 12 10 8 6 2 0 0 40 60 100 120 Q_G, Total Gate Charge (nC)

Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage



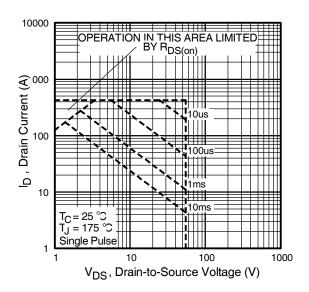


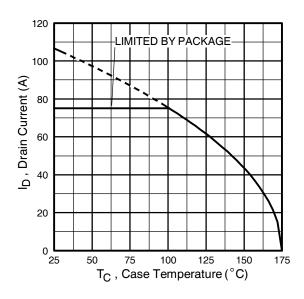
Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

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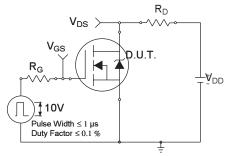


Fig 10a. Switching Time Test Circuit

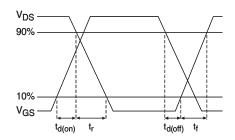


Fig 9. Maximum Drain Current Vs. Case Temperature

Fig 10b. Switching Time Waveforms

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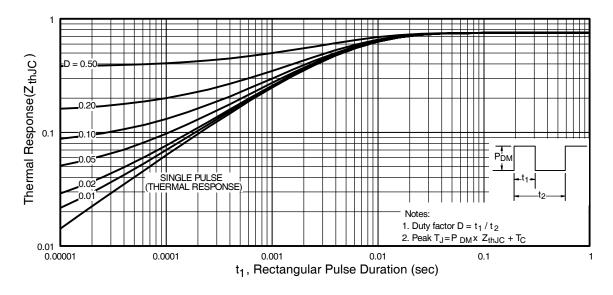


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

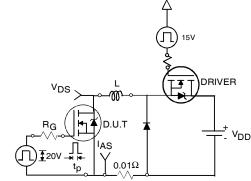


Fig 12a. Unclamped Inductive Test Circuit

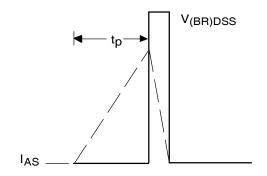


Fig 12b. Unclamped Inductive Waveforms

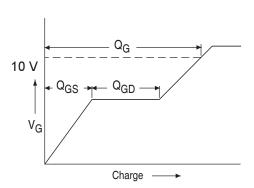


Fig 13a. Basic Gate Charge Waveform

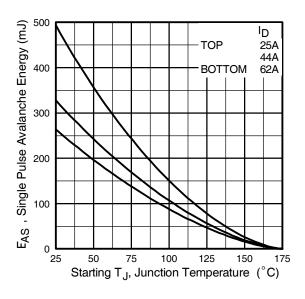


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

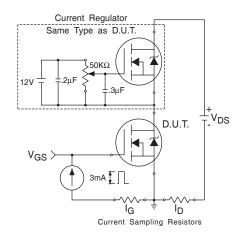
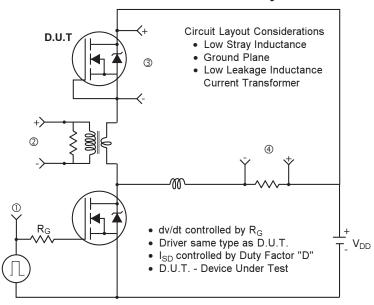
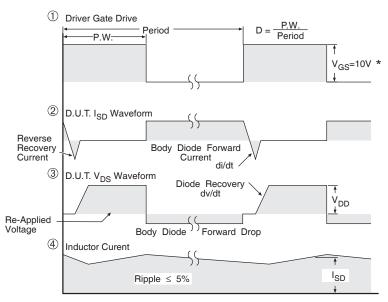


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit





* V_{GS} = 5V for Logic Level Devices

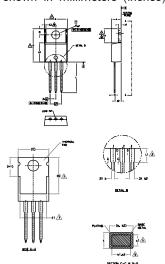
Fig 14. For N-Channel HEXFETS

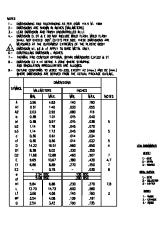
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TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

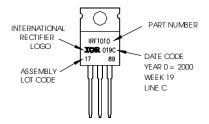




TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010 LOT CODE 1789 ASSEMBLED ON WW 19, 2000 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"



TO-220AB package is not recommended for Surface Mount Application

Notes:

- 1. For an Automotive Qualified version of this part please seehttp://www.irf.com/product-info/auto/
- 2. For the most current drawing please refer to IR website at http://www.irf.com/package/

Data and specifications subject to change without notice. This product has been designed and qualified for the Industrial market.

Qualification Standards can be found on IR's Web site.



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